



40V 2.0mΩ N-Ch Power MOSFET

Features

- Ultra-low $R_{DS(ON)}$
- Low Gate Charge
- 100% UIS Tested, 100% R_g Tested
- Pb-free Lead Plating
- Halogen-free and RoHS-compliant

Product Summary

Parameter	Value	Unit
V_{DS}	40	V
$V_{GS(th_Typ)}$	1.5	V
I_D (@ $V_{GS} = 10V$) ⁽¹⁾	119	A
$R_{DS(ON_Typ)}$ (@ $V_{GS} = 10V$)	2.0	mΩ
$R_{DS(ON_Typ)}$ (@ $V_{GS} = 4.5V$)	2.7	mΩ

Applications

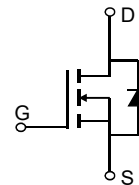
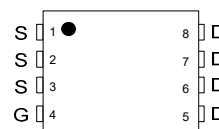
- Power Management in Computing, CE, IE 4.0, Communications
- Current Switching in DC/DC & AC/DC (SR) Sub-systems
- Load Switching, Quick/Wireless Charging, Motor Driving

PDFN3x3-8L



Pin Configuration

Top View

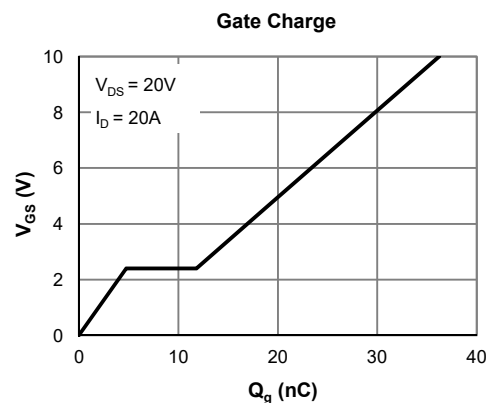
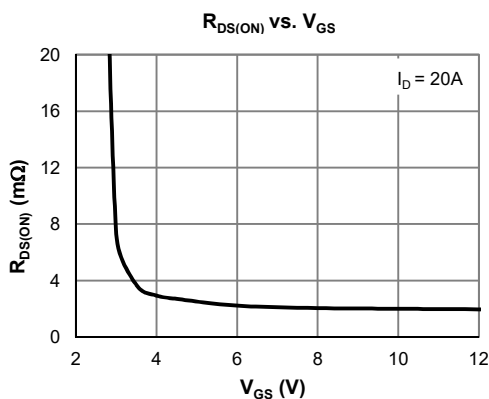


Ordering Information

Device	Package	# of Pins	Marking	MSL	T_J (°C)	Media	Quantity (pcs)
JMSL0402AU-13	PDFN3x3-8L	8	SL0402A	1	-55 to 150	13-inch Reel	3000

Absolute Maximum Ratings (@ $T_A = 25^\circ C$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DS}	40	V
Gate-to-Source Voltage	V_{GS}	±20	V
Continuous Drain Current ⁽¹⁾	I_D	$T_C = 25^\circ C$	119
		$T_C = 100^\circ C$	76
Pulsed Drain Current ⁽²⁾	I_{DM}	471	A
Avalanche Current ⁽³⁾	I_{AS}	29	A
Avalanche Energy ⁽³⁾	E_{AS}	126	mJ
Power Dissipation ⁽⁴⁾	P_D	$T_C = 25^\circ C$	66
		$T_C = 100^\circ C$	26
Junction & Storage Temperature Range	T_J, T_{STG}	-55 to 150	°C



**Electrical Characteristics** (@ $T_J = 25^\circ\text{C}$ unless otherwise specified)

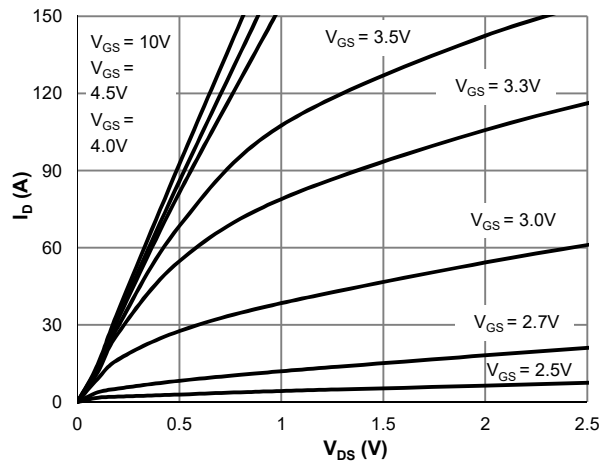
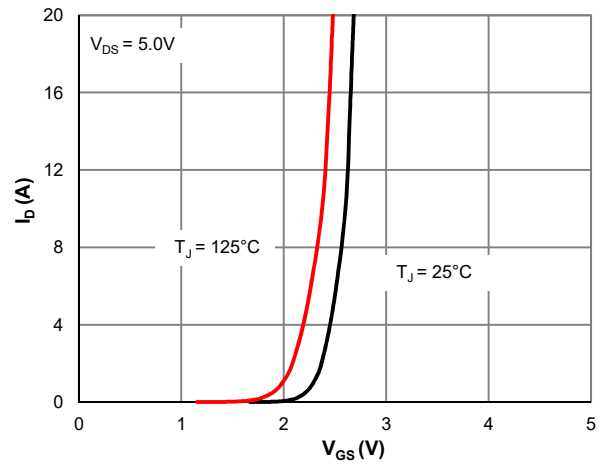
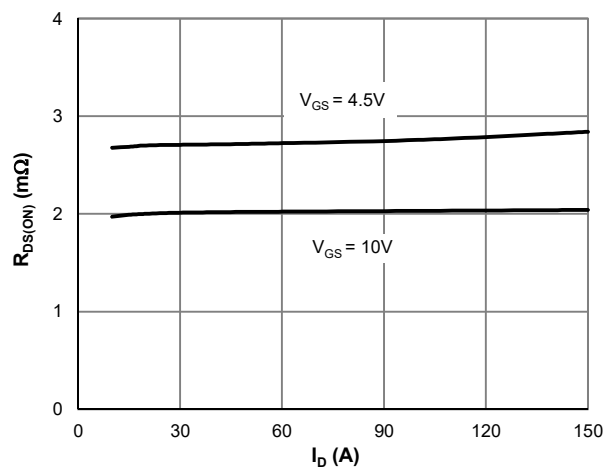
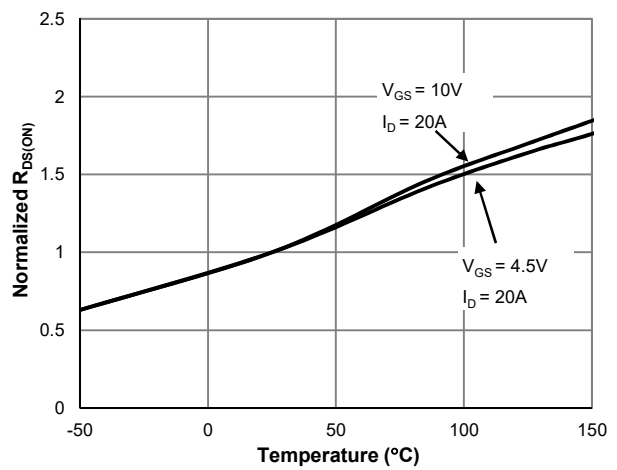
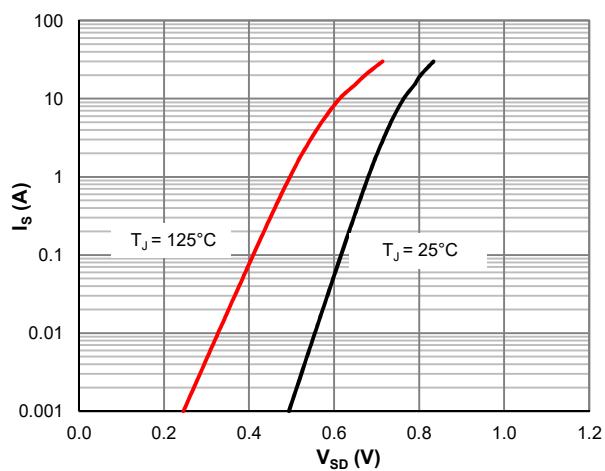
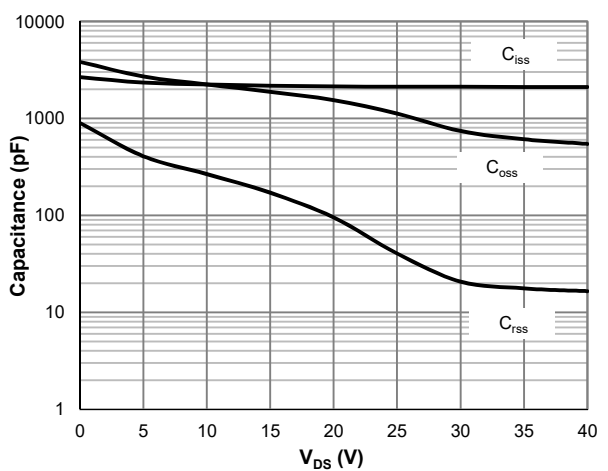
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
STATIC PARAMETERS						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$	40			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 32\text{V}, V_{GS} = 0\text{V}$ $T_J = 55^\circ\text{C}$			1.0 5.0	μA
Gate-Body Leakage Current	I_{GSS}	$V_{DS} = 0\text{V}, V_{GS} = \pm 20\text{V}$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	1.2	1.5	2.5	V
Static Drain-Source ON-Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{V}, I_D = 20\text{A}$		2.0	2.5	m Ω
		$V_{GS} = 4.5\text{V}, I_D = 20\text{A}$		2.7	3.5	m Ω
Forward Transconductance	g_{FS}	$V_{DS} = 5\text{V}, I_D = 20\text{A}$		136		S
Diode Forward Voltage	V_{SD}	$I_S = 1\text{A}, V_{GS} = 0\text{V}$		0.70	1.0	V
Diode Continuous Current	I_S	$T_C = 25^\circ\text{C}$			66	A
DYNAMIC PARAMETERS ⁽⁵⁾						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{V}, V_{DS} = 20\text{V}, f = 1\text{MHz}$		2131		pF
Output Capacitance	C_{oss}			1538		pF
Reverse Transfer Capacitance	C_{rss}			95		pF
Gate Resistance	R_g	$V_{GS} = 0\text{V}, V_{DS} = 0\text{V}, f = 1\text{MHz}$		1.3		Ω
SWITCHING PARAMETERS ⁽⁵⁾						
Total Gate Charge (@ $V_{GS} = 10\text{V}$)	Q_g	$V_{GS} = 0 \text{ to } 10\text{V}$ $V_{DS} = 20\text{V}, I_D = 20\text{A}$		36		nC
Total Gate Charge (@ $V_{GS} = 4.5\text{V}$)	Q_g			18.6		nC
Gate Source Charge	Q_{gs}			4.7		nC
Gate Drain Charge	Q_{gd}			7.1		nC
Turn-On DelayTime	$t_{D(on)}$	$V_{GS} = 10\text{V}, V_{DS} = 20\text{V}$ $R_L = 1.0\Omega, R_{GEN} = 6\Omega$		5.5		ns
Turn-On Rise Time	t_r			8.7		ns
Turn-Off DelayTime	$t_{D(off)}$			31		ns
Turn-Off Fall Time	t_f			15.8		ns
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 15\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$		39		ns
Body Diode Reverse Recovery Charge	Q_{rr}	$I_F = 15\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$		28		nC

Thermal Performance

Parameter	Symbol	Typ.	Max.	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	55	70	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.6	1.9	$^\circ\text{C}/\text{W}$

Notes:

1. Computed continuous current assumes the condition of T_{J_Max} while the actual continuous current depends on the thermal & electro-mechanical application board design.
2. This single-pulse measurement was taken under $T_{J_Max} = 150^\circ\text{C}$.
3. This single-pulse measurement was taken under the following condition [$L = 300\mu\text{H}, V_{GS} = 10\text{V}, V_{DD} = 20\text{V}$] while its value is limited by $T_{J_Max} = 150^\circ\text{C}$.
4. The power dissipation P_D is based on $T_{J_Max} = 150^\circ\text{C}$.
5. This value is guaranteed by design hence it is not included in the production test.

Typical Electrical & Thermal Characteristics

Figure 1: Saturation Characteristics

Figure 2: Transfer Characteristics

Figure 3: $R_{DS(ON)}$ vs. Drain Current

Figure 4: $R_{DS(ON)}$ vs. Junction Temperature

Figure 5: Body-Diode Characteristics

Figure 6: Capacitance Characteristics

Typical Electrical & Thermal Characteristics

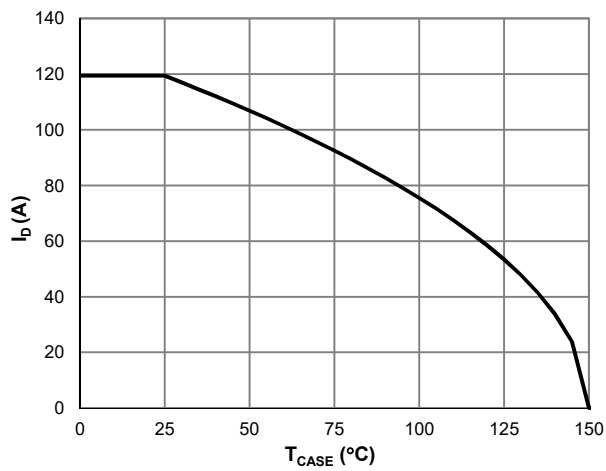


Figure 7: Current De-rating

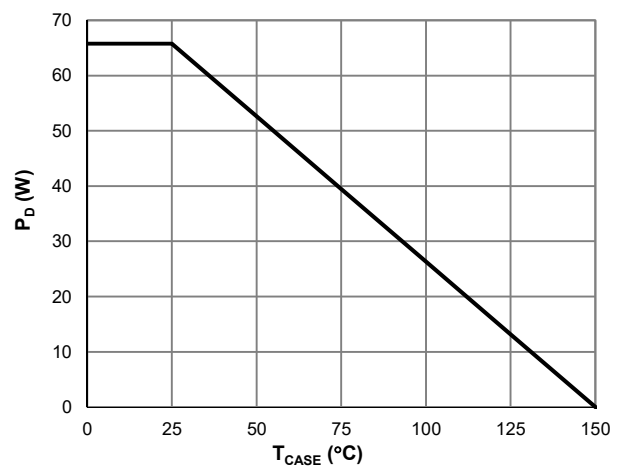


Figure 8: Power De-rating

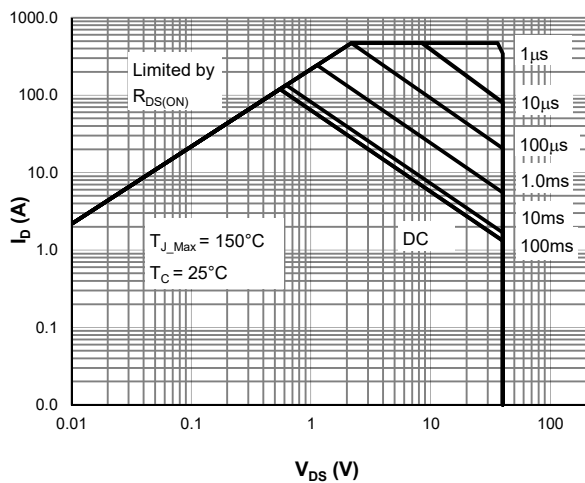


Figure 9: Maximum Safe Operating Area

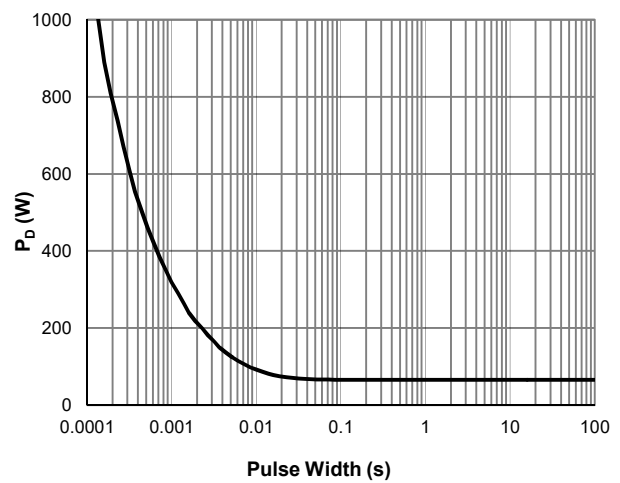


Figure 10: Single Pulse Power Rating, Junction-to-Case

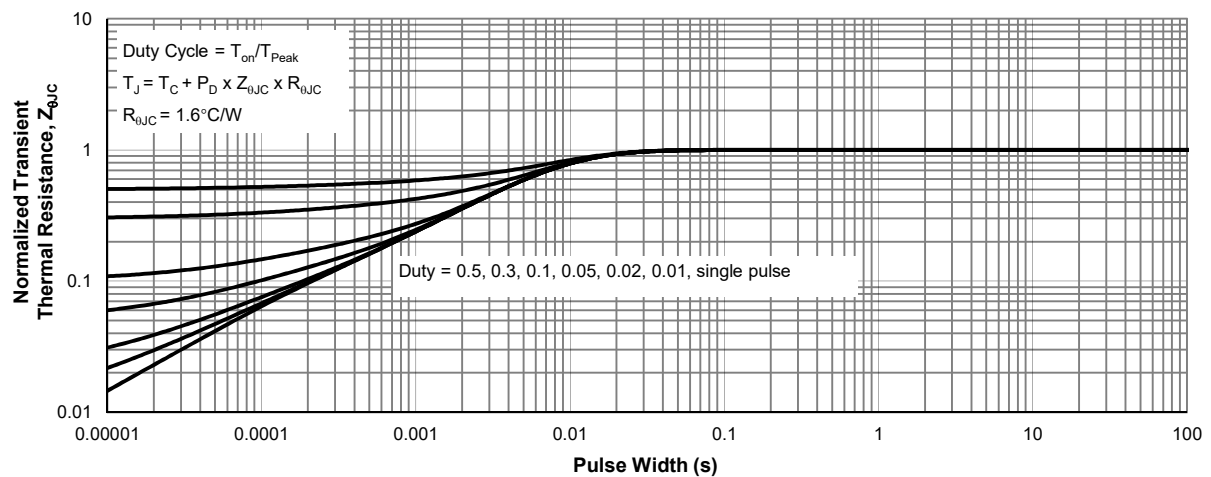
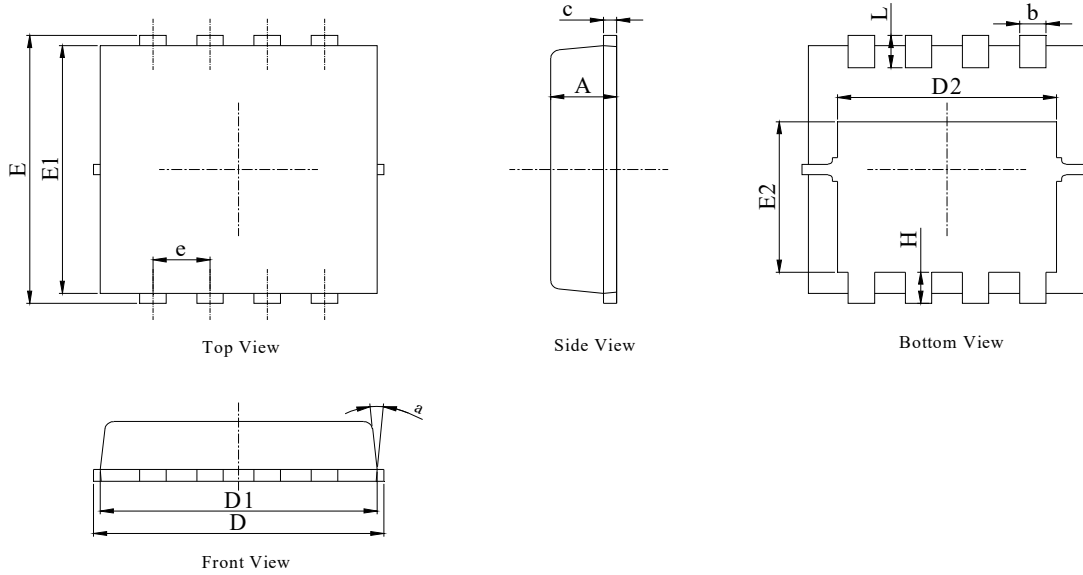
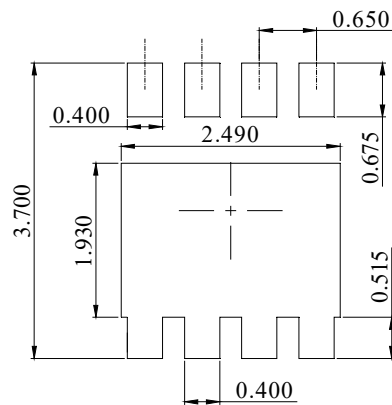


Figure 11: Normalized Maximum Transient Thermal Impedance

PDFN3x3-8L Package Information
Package Outline

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
2. ALL DIMNESIONS IN MILLIMETER (ANNGL E IN DEGREE).
3. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

DIM.	MILLIMETER		
	MIN.	NOM.	MAX.
A	0.70	0.75	0.80
b	0.25	0.30	0.35
c	0.10	0.20	0.25
D	3.00	3.15	3.25
D1	2.95	3.05	3.15
D2	2.39	2.49	2.59
E	3.20	3.30	3.40
E1	2.95	3.05	3.15
E2	1.70	1.80	1.90
e	0.65 BSC		
H	0.30	0.40	0.50
L	0.25	0.40	0.50
a	---	---	15°

Recommended Soldering Footprint


DIMENSIONS: MILLIMETERS